

PTO/SB/08A (08-03)

Substitute for form 1449/PTO				<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use as many sheets as necessary)				Application Number	10/826,811
				Filing Date	7/23/2003
				First Named Inventor	Christopher L. Chua
				Art Unit	2828
				Examiner Name	Tuan N. Nguyen
				Attorney Docket Number	A3316-US-NP
Sheet	1	of	1		

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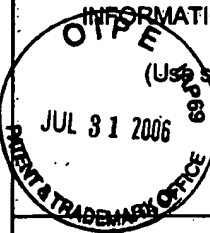
Non Patent Literature Documents			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	?
TU		D.L. HUFFAKER, ET AL.: Appl. Phys. Lett, Vol 65, no 1 pp 97-99, 1994	<input type="checkbox"/>
TN		G.R. HADLEY: Optic Letters, Vol 20, no 13, pp 1483-1485, 1995	<input type="checkbox"/>
TU		S. MUKAI, ETAL: Appl Phys. Lett, Vol 45, no8, pp834-835, 1984	<input type="checkbox"/>
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Examiner Signature	<i>[Signature]</i>	Date Considered	8/23/02
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**\*EXAMINER:** Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Applicant's unique citation description number (optional). <sup>2</sup> Applicant is to place a check mark here if English Translation is attached.

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Form PTO-1449 (REV. 1/06)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. A3316-US-NP	APPLICATION NO. 10/625,811
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANT(S) Christopher L. Chua	
				FILING DATE 7/23/2003	GROUP 2828
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	52	JP 10-229248	08/25/1998	Japan	Y	Y
	53	EP 0 858 137 A3	04/19/2000	EPO		

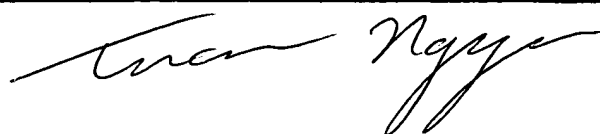
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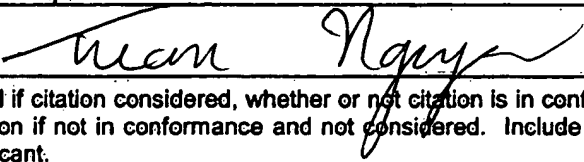
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<p>Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>		